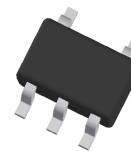


# UMC5N

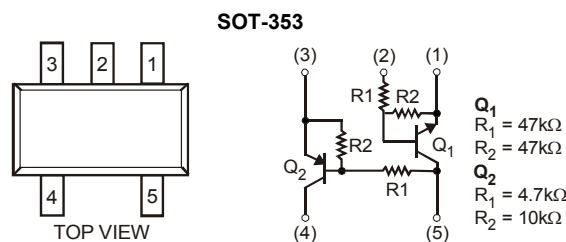
## Features

- Epitaxial Planar Die Construction
- Surface Mount Package Suited for Automated Assembly
- Simplifies Circuit Design and Reduces Board Space
- **Lead Free/RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**



## Mechanical Data

- Case: SOT-353
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Annealed Over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.006 grams (approximate)



## Maximum Ratings, Total Device @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3)	$P_D$	150	mW
Thermal Resistance, Junction to Ambient Air (Note 3)	$R_{\theta JA}$	833	$^\circ\text{C/W}$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

## Maximum Ratings, Pre-Biased NPN Transistor, $Q_1$ @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Supply Voltage	$V_{CC}$	50	V
Input Voltage	$V_{IN}$	-10 to +40	V
Output Current	$I_O$	30	mA
Collector Current	$I_{C(MAX)}$	100	mA

## Maximum Ratings, Pre-Biased PNP Transistor, $Q_2$ @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Supply Voltage	$V_{CC}$	-50	V
Input Voltage	$V_{IN}$	-20 to +7	V
Output Current	$I_O$	-100	mA
Collector Current	$I_{C(MAX)}$	-100	mA

- Notes:
1. No purposefully added lead.
  2. Diodes Inc.'s "Green" policy can be found on our website at [www.twtysemi.com](http://www.twtysemi.com)
  3. Device mounted on FR-4 PCB; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at [www.twtysemi.com](http://www.twtysemi.com)

# UMC5N

## Electrical Characteristics, Pre-Biased NPN Transistor, Q<sub>1</sub> @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Input Voltage	V <sub>I(off)</sub>	—	—	0.5	V	V <sub>CC</sub> = 5V, I <sub>O</sub> = 100μA
	V <sub>I(on)</sub>	3	—	—	V	V <sub>O</sub> = 0.3V, I <sub>O</sub> = 2mA
Output Voltage	V <sub>O(on)</sub>	—	0.1	0.3	V	I <sub>O</sub> /I <sub>I</sub> = 10mA/0.5 mA
Input Current	I <sub>I</sub>	—	—	0.18	mA	V <sub>I</sub> = 5V
Output Current	I <sub>O(off)</sub>	—	—	0.5	μA	V <sub>CC</sub> = 50V, V <sub>I</sub> = 0V
DC Current Gain	G <sub>I</sub>	68	—	—	—	V <sub>O</sub> = 5V, I <sub>O</sub> = 5mA
Gain-Bandwidth Product	f <sub>T</sub>	—	250	—	MHz	V <sub>CE</sub> = 10V, I <sub>E</sub> = -5mA, f = 100MHz*
Input Resistance	R <sub>1</sub>	32.9	47	61.1	kΩ	—
Resistance Ratio	R <sub>2</sub> /R <sub>1</sub>	0.8	1	1.2	—	—

\*Characteristics of Transistor – for reference only.

## Electrical Characteristics, Pre-Biased PNP Transistor, Q<sub>2</sub> @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Input Voltage	V <sub>I(off)</sub>	—	—	-0.3	V	V <sub>CC</sub> = -5V, I <sub>O</sub> = -100μA
	V <sub>I(on)</sub>	-2.5	—	—	V	V <sub>O</sub> = -0.3V, I <sub>O</sub> = -20mA
Output Voltage	V <sub>O(on)</sub>	—	-0.1	-0.3	V	I <sub>O</sub> /I <sub>I</sub> = -10mA/-0.5 mA
Input Current	I <sub>I</sub>	—	—	-1.8	mA	V <sub>I</sub> = -5V
Output Current	I <sub>O(off)</sub>	—	—	-0.5	μA	V <sub>CC</sub> = -50V, V <sub>I</sub> = 0V
DC Current Gain	G <sub>I</sub>	30	—	—	—	V <sub>O</sub> = -5V, I <sub>O</sub> = -10mA
Gain-Bandwidth Product	f <sub>T</sub>	—	250	—	MHz	V <sub>CE</sub> = -10V, I <sub>E</sub> = 5mA, f = 100MHz*
Input Resistance	R <sub>1</sub>	3.29	4.7	6.11	kΩ	—
Resistance Ratio	R <sub>2</sub> /R <sub>1</sub>	1.7	2.1	2.6	—	—

\*Characteristics of Transistor – for reference only.